

SEMiX191KD16s



SEMiX® 1s

Rectifier Diode Module SEMiX191KD16s

Features

Terminal height 17 mm
Chips soldered directly to isolated substrate

Typical Applications*

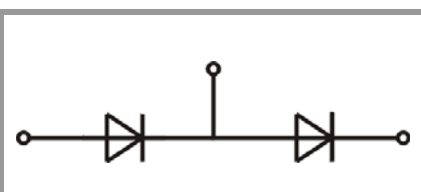
- Input Bridge Rectifier for AC/DC motor control
- Power supply

Absolute Maximum Ratings

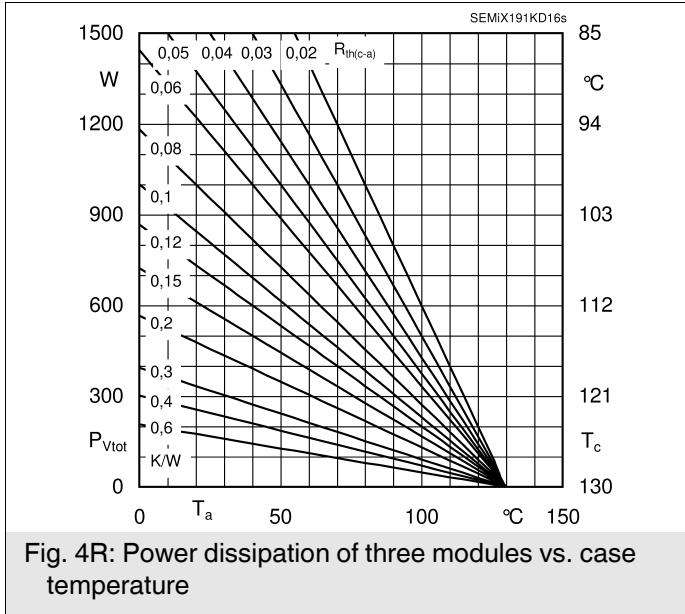
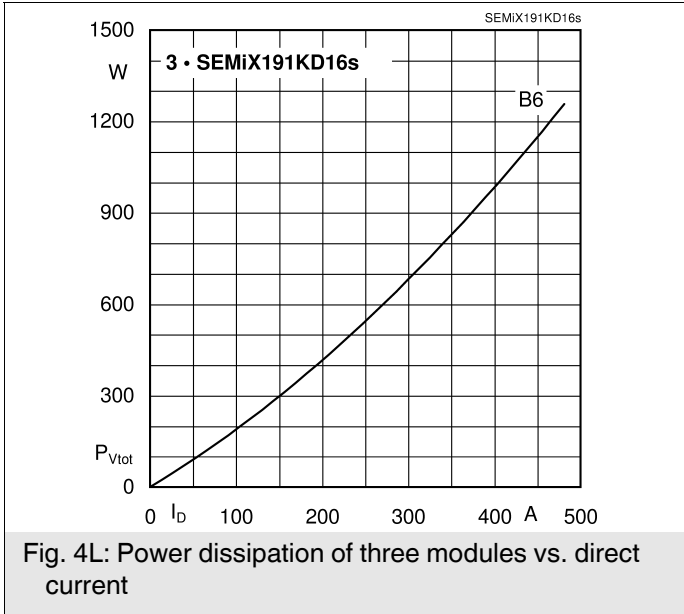
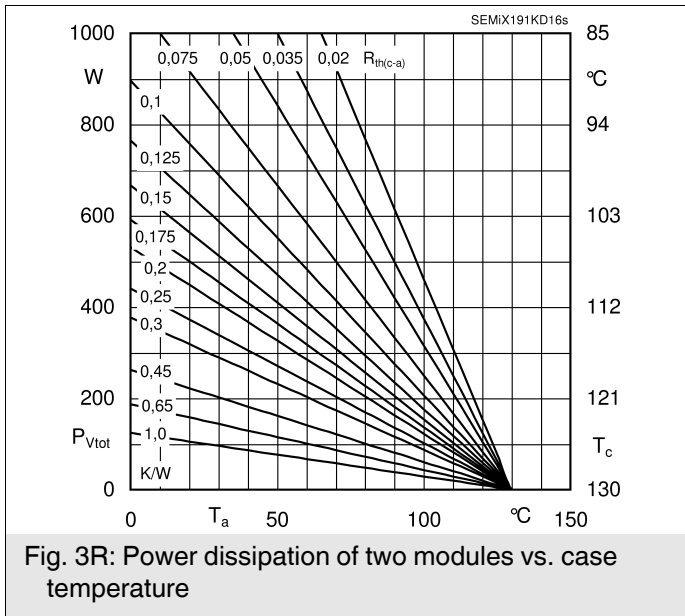
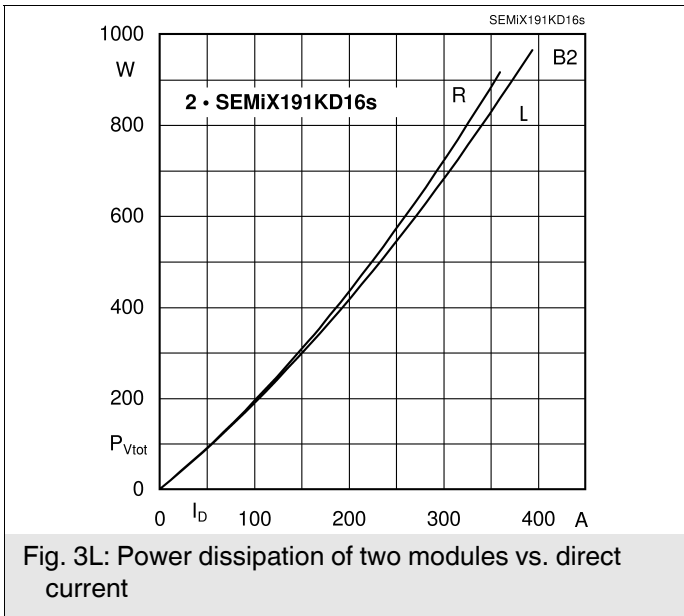
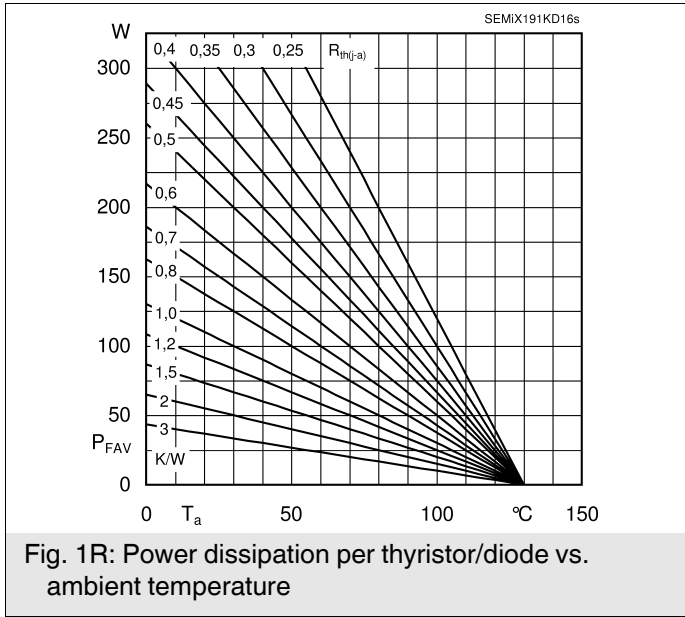
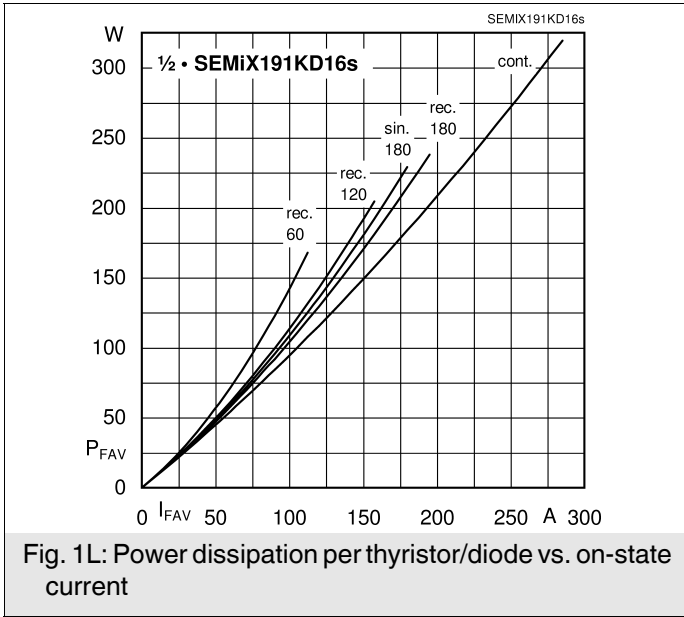
Symbol	Conditions		Values	Unit
Rectifier Diode				
I_{FAV}	sin. 180°	$T_c = 85\text{ °C}$	190	A
		$T_c = 100\text{ °C}$	145	A
I_{FSM}	10 ms	$T_j = 25\text{ °C}$	6000	A
		$T_j = 130\text{ °C}$	5000	A
i^2t	10 ms	$T_j = 25\text{ °C}$	180000	A ² s
		$T_j = 130\text{ °C}$	125000	A ² s
V_{RSM}			1700	V
V_{RRM}			1600	V
T_j			-40 ... 130	°C
Module				
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Diode					
V_F	$T_j = 25\text{ °C}, I_F = 500\text{ A}$			1.5	V
$V_{(TO)}$	$T_j = 130\text{ °C}$			0.85	V
r_T	$T_j = 130\text{ °C}$			0.95	mΩ
I_{RD}	$T_j = 130\text{ °C}, V_{RD} = V_{RRM}$			12	mA
$R_{th(j-c)}$					K/W
					K/W
$R_{th(j-c)}$	sin. 180			0.18	K/W
					K/W
Module					
$R_{th(c-s)}$	per chip				K/W
	per module		0.075		K/W
M_s	to heat sink (M5)	3		5	Nm
M_t	to terminals (M6)	2.5		5	Nm
a				5 * 9,81	m/s ²
w			145		g



KD



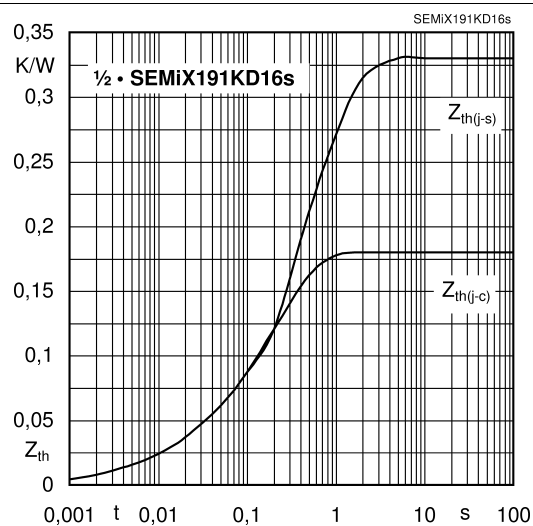


Fig. 6: Transient thermal impedance vs. time

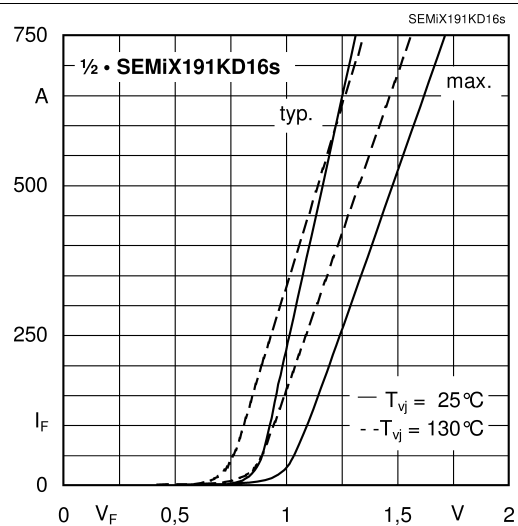


Fig. 7: On-state characteristics

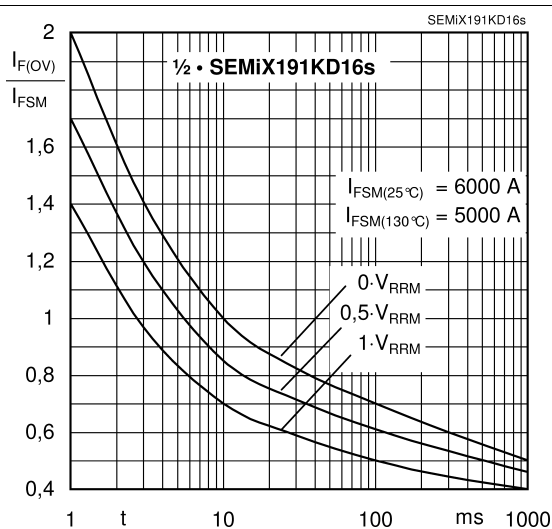
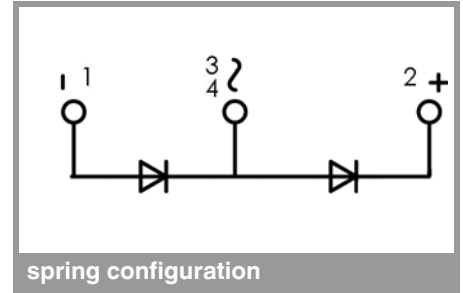
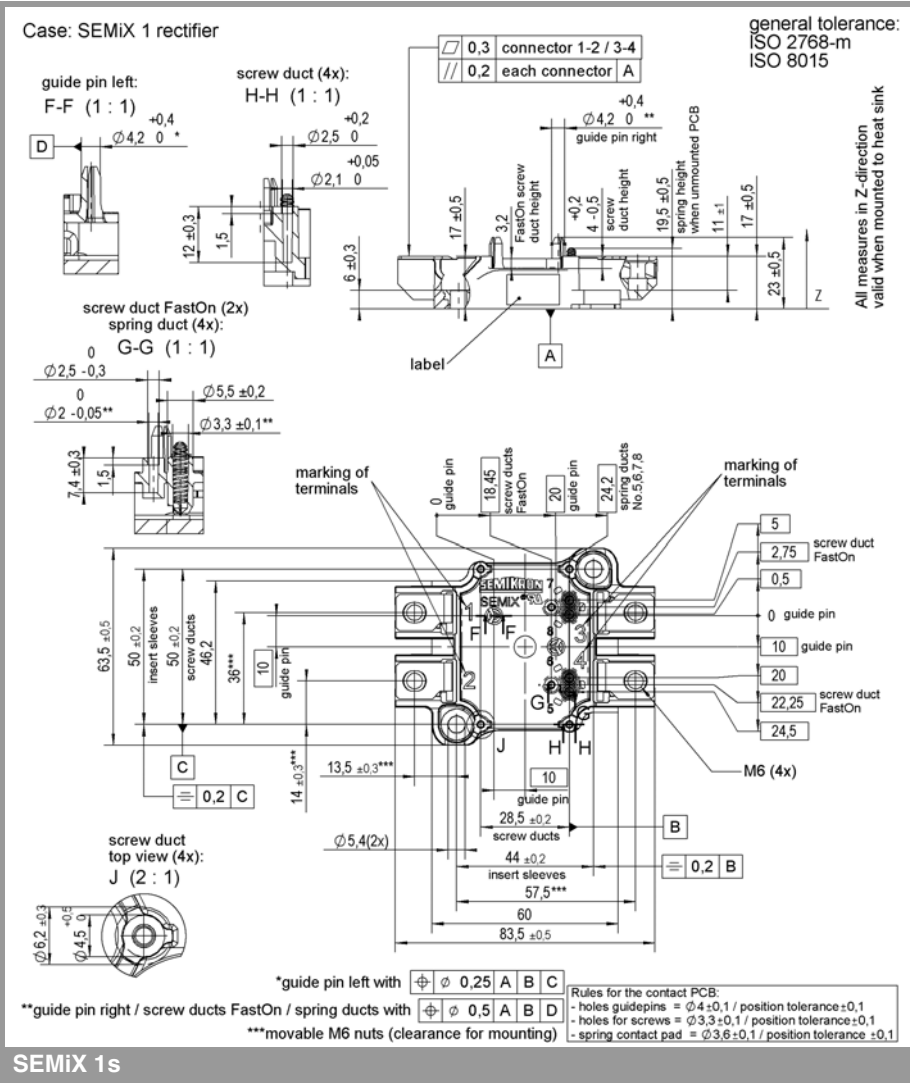


Fig. 8: Surge overload current vs. time



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.